

JL7018M Datasheet

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JL7018M Features

CPU

- 32bit Dual-Core DSP
- Maximum speed 160MHz
- IEEE754 Single precision FPU
- Mathematical accelerate engine
- Interrupts with 8 priority level

Memory

- Support MMU
- Built-In Flash

Clocks

- On-chip 16 MHz clock oscillator
- On-chip 200 kHz lower-temperature-drift clock oscillator
- 24 MHz crystal oscillator

DSP Audio Processing

- LDAC, LHDC, SBC, AAC Audio decodes supported for BT audio
- mSBC voice codec supported for BT phone
- Supports MP2, MP3, WMA, APE, FLAC, AAC, MP4, M4A, WAV, AIF, AIFC audio decoding
- Packet Loss Concealment (PLC) for voice processing
- Single/Dual MIC Environmental Noise Cancellation (ENC)
- Multi-band DRC limiter
- Multi-band EQ configuration for voice Effects
- Support Hi-Res Audio

Audio Codec

- Two channels 24-bit DAC, SNR \geq 104dB
- Four channels 24-bit ADC, SNR \geq 95dB
- Audio DAC Sampling rates of 8kHz/11.025kHz/16kHz/22.05kHz/24kHz/32kHz/44.1kHz/48kHz/64kHz/88.2kHz/96kHz are supported
- Audio ADC Sampling rates of

8kHz/11.025kHz/16kHz/22.05kHz/24kHz/32kHz/44.1kHz/48kHz are supported

- Support four digital/analog MIC inputs
- Four channels analog audio inputs
- Audio DAC supports differential cap-less mode or single-ended mode
- Direct drive 16ohm/32ohm Speaker loading

ANC

- ANC processing engine up to 750 kHz sample rate
- 7.5 μ s analog to analog latency
- Supports 4 differential or single-ended analog inputs, 4 digital microphone inputs for ANC
- Supports 2 channels Feed-Forward, Feed-Back, Hybrid ANC
- ANC module include 20 double precision Biquad filters for each FF/FB/ music compensation control

Bluetooth

- Compliant with Bluetooth V5.4+BR+EDR+BLE specification (QDID: 222830)
- Support AoA/AoD direction finding
- Support LE audio BIS/CIS full function
- Meet class1, class2, class3 transmitting power requirement
- Maximum +9dbm transmitting power
- EDR receiver with minimum -95dBm sensitivity
- Support a2dp\avctp\avdtp\avrcp\hfp\spp\smpl\att\gap\gatt\rfcomm\sdpl2cap profile
- BAP 1.0.1\PACS 1.0.1\CCP 1.0\MCP 1.0\MICP 1.0\VCP 1.0\CSIP 1.0.1\ASCS1.0\BASS 1.0\CAP 1.0\HAP 1.0\PBP 1.0\TMAP 1.0\LC3 1.0
- A2DP 1.4\AVCTP 1.4\AVDTP 1.3\AVRCP 1.6.2\HFP 1.8\SPP 1.2\RFCOMM 1.2\PNP 1.3\HID 1.1.1\SDP core5.4\L2CAP core 5.4

Peripherals

- One full speed USB OTG controller
- One SD host controller for eMMC/SD
- Six multi-function 32-bit timers, support capture and PWM mode
- Four UART interface, UART0,UART1&UART2 support DMA
- I2C Master/Slave interface
- SPI Master/Slave interface
- I2S Master/Slave interface
- QDEC
- Low power CapSense
- 12-channel 10-bit ADC for analog sampling
- 4-channel Motor PWM controller
- 24 Individually programmable and multiplexed GPIO pins
- Up to 12 external interrupt/wake-up source(low power available,can be multiplexed to any I/O)

PMU

- Built-in lithium battery charging manager,up to 200mA charging current
- Built-in LDO and Buck DC-DC converter
- Less than 2uA sleep current
- VPWR range : 4.5V to 5.5V
- VBAT range : 2.2V to 4.5V
- IOVDD range : 2.2V to 3.6V
- Conform with IEC 62368-1:2018 certification

Packages

- QFN40(5mm*5mm)

Temperature

- Operating temperature: -40°C to +85°C
- Storage temperature: -65°C to +150°C

Applications

- Bluetooth Stereo Headsets and Headphones
- Bluetooth Stereo ANC Headsets and Headphones
- Wireless microphone

1 Block Diagram

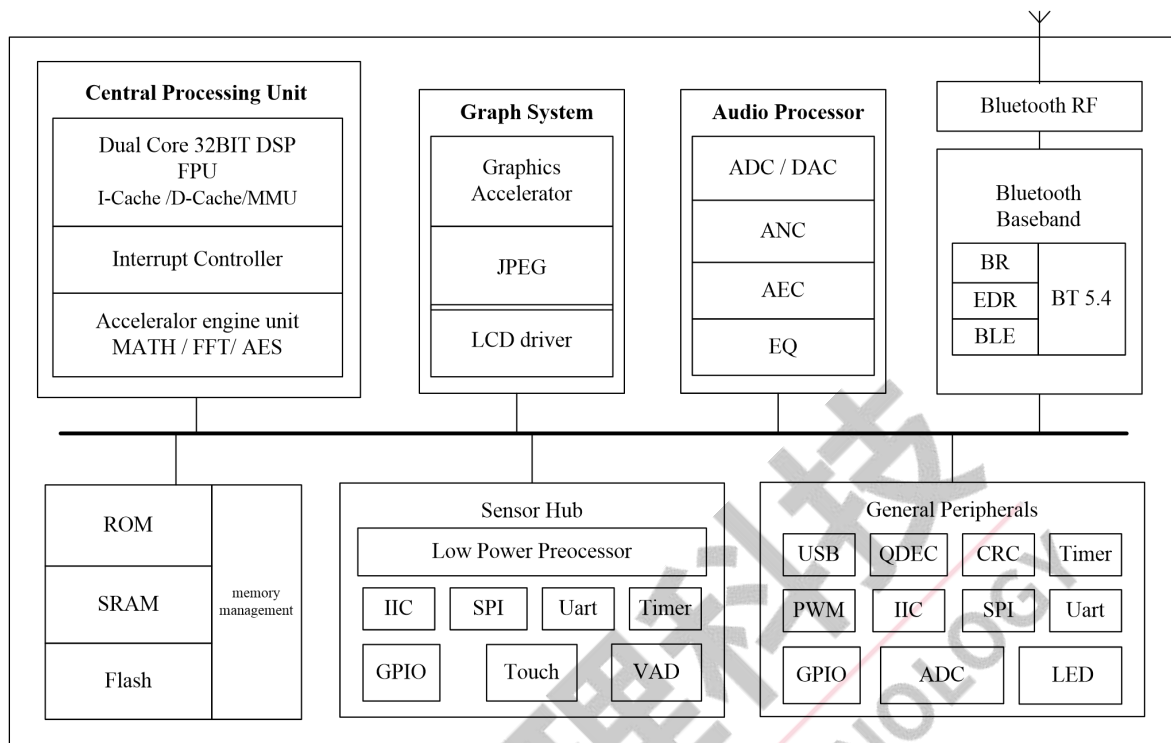


Figure 1-1 JL7018M Block Diagram

2 Pin Definition

2.1 Pin Assignment

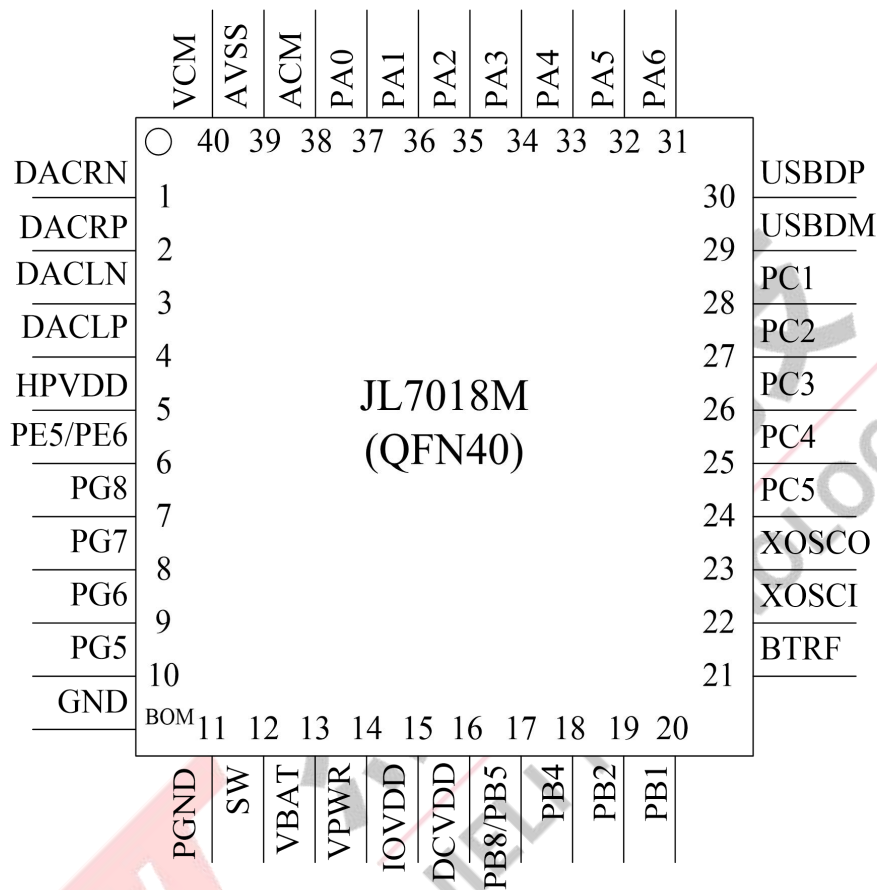


Figure 2-1 JL7018M Package Diagram

2.2 Pin Description

Table 2-1 JL7018M Pin Description

PIN NO.	Name	Type	Function	Other Function
1	DACRN	AO		Different DAC Right Negative Channel
2	DACRP	AO		Different DAC Right Positive Channel
3	DACLN	AO		Different DAC Left Negative Channel
4	DACLP	AO		Different DAC Left Positive Channel
5	HPVDD	PI		Audio power
6	PE6	I/O	GPIO	SDPG: supply voltage to SD Card
	PE5	I/O	GPIO	SPI4_D3(PSRAM): SPI4 Data3; SPI0_DAT3D: SPI0 Data3(D);
7	PG8	I/O	GPIO	MICIN2: MIC2 Input Channel 2; MIC2_P: Different MIC2 Positive; AMUX_C0: Analog Channel C0 input;
8	PG7	I/O	GPIO	MIC_BIAS2: MIC2 Bias Output(Built-in resistor); MIC2_N: Different MIC2 Negative; AMUX_C1: Analog Channel C1 input; ADC15: ADC Input Channel 15;
9	PG6	I/O	GPIO	MICIN3: MIC3 Input Channel3; MIC3_P: Different MIC3 Positive; AMUX_D0: Analog Channel D0 input; FPIN2: Fault Detect In2;
10	PG5	I/O	GPIO	MIC_BIAS3: MIC3 Bias Output(Built-in resistor); MIC3_N: Different MIC3 Negative; AMUX_D1: Analog Channel D1 input; ADC14: ADC Input Channel 14; TMR3CK: PWM Timer3 CLK In;
11	PGND	G		The ground of Buck DC-DC converter;
12	SW	PO		Switch signal of the Buck converter,connected to Inductor;
13	VBAT	P		Power Supply, connect to battery;
14	VPWR (PP0)	PI (I/O)	GPIO (High Voltage Resistant)	Charging Power Input; UART0TXB: Uart0 Data Out(B); UART0RXB: Uart0 Data In(B); PWM3: Timer3 PWM Output; CAP1: Timer1 Capture;
15	IOVDD	PO		Built-in linear voltage regulator output;
16	DCVDD	P		Internal Power;

17	PB8	I/O	GPIO	EVDD: Supply voltage 1.1V; CAP4: Timer4 Capture;
	PB5	I/O	GPIO	LP_Touch4: Low Power Touch Channel 4; IIC1_SDA_A: IIC1 SDA(A); ADC8: ADC Input Channel 8; UART3RXB: Uart3 Data In(B);
18	PB4	I/O	GPIO	LP_Touch3: Low Power Touch Channel 3; CLKOUT0: CLK Output Channel 0; SPI4DIA: SPI4 Data In(A); IIC1_SCL_A: IIC1 SCL(A); UART3TXB: Uart3 Data Out(B); TMR2: Timer2 Clock Input;
19	PB2	I/O	GPIO	LP_Touch2: Low Power Touch Channel 2; SPI4CLKA: SPI4 Clock(A); Q-decoder0_0: Quadrature decoder0_0; ADC7: ADC Input Channel 7; UART3TXA: Uart3 Data Out(A); CAP5: Timer5 Capture;
20	PB1	I/O	GPIO	Hold down 0 to reset; LP_Touch1: Low Power Touch Channel 1; ADC6: ADC Input Channel 6;
21	BTRF	RFI		Bluetooth RF antenna interface;
22	XOSCI	I		System Crystal Oscillator Input;
23	XOSCO	O		System Crystal Oscillator Output;
24	PC5	I/O	GPIO	SPI0_DAT2C: SPI0 Data2(C); SD0_CLKA: SD0 Clock(A); SPI1DOB: SPI1 Data Out(B); IIC0_SDA_B: IIC0 SDA(B); ALNK_DAT3(B): Audio Link Data3(B); ADC5: ADC Input Channel 5; UART2RXA: Uart2 Data In(A);
25	PC4	I/O	GPIO	SPI0_DIC: SPI0 Data In(C); SD0CMDA: SD0 CMD(A); SPI1CLKB: SPI1 Clock(B); IIC0_SCL_B: IIC0 SCL(B); ALNK_DAT2B: Audio Link Data2(B); ADC4: ADC Input Channel 4; UART2TXA: Uart2 Data Out(A); PWM4: Timer4 PWM Output;

26	PC3	I/O	GPIO	SPI0_CSC: SPI0 Chip Select(C); SD0DATOA: SD0 Data Out(A); SPI1DIB: SPI1 Data In(B); ALNK_LRCKB: Audio Link Word Select(B); TMR3: Timer3 Clock Input;
27	PC2	I/O	GPIO	SPI0_DOC: SPI0 Data Out(C); ALNK_SCLKB: Audio Link Serial Clock(B); TMR1: Timer1 Clock Input;
28	PC1	I/O	GPIO	SPI0_CLKC: SPI0 Clock(C); ALNK_DAT1B: Audio Link Data1(B); TMR5: Timer5 Clock Input; PWMCH1L: PWM CH1 Low;
29	USBDM	I/O	USB Negative Data (pull down)	SDTAP_DATB: SDTAP Data(B); SPI2DOB: SPI2 Data Out(B); IIC0_SDA_A: IIC0 SDA(A); ADC11: ADC Input Channel 11; UART1RXB: Uart1 Data In(B);
30	USBDP	I/O	USB Positive Data (pull down)	SDTAP_CLKB: SDTAP CLK(B); SPI2CLKB: SPI2 Clock(B); IIC0_SCL_A: IIC0 SCL(A); ADC10: ADC Input Channel 10; UART1TXB: Uart1 Data Out(B);
31	PA6	I/O	GPIO	PLNK_DAT0: PLNK Data 0; SPI2DOA: SPI2 Data Out(A); ALNK_DAT3A: Audio Link Data3(A); ADC2: ADC Input Channel 2; UART0RXA: Uart0 Data In(A); CAP0: Timer0 Capture;
32	PA5	I/O	GPIO	PLNK_SCLK: PLNK Serial Clock; SPI2CLKA: SPI2 Clock(A); ALNK_DAT2A: Audio Link Data2(A); ADC1: ADC Input Channel 1; UART0TXA: Uart0 Data Out(A);
33	PA4	I/O	GPIO	MIC_BIAS1: MIC1 Bias Output(Built-in resistor); MIC1_N: Different MIC1 Negative; AMUX_B1: Analog Channel B1 input; SPI2DIA: SPI2 Data In(A); ALNK_DAT1A: Audio Link Data1(A); CAP2: Timer2 Capture;

34	PA3	I/O	GPIO	MICIN1: MIC1 Input Channel 1; MIC1_P: Different MIC1 Positive; AMUX_B0: Analog Channel B0 input; SPI1DOA: SPI1 Data Out(A); ALNK_DAT0(A): Audio Link Data0(A); PWM1: Timer1 PWM Output;
35	PA2	I/O	GPIO	MIC_BIAS0: MIC0 Bias Output(Built-in resistor); MIC0_N: Different MIC0 Negative; AMUX_A1: Analog Channel A1 input; CLKOUT1: Clock Out1; SPI1CLKA: SPI1 Clock(A); ALNK_MCLKA: ALNK Master Clock(A); UART1RXA: Uart1 Data In(A); CAP3: Timer3 Capture;
36	PA1	I/O	GPIO	MICIN0: MIC0 Input Channel 0; MIC0_P: Different MIC0 Positive; AMUX_A0: Analog Channel A0 input; SPI1DIA: SPI1 Data In(A); UART1TXA: Uart1 Data Out(A); PWM0: Timer0 PWM Output;
37	PA0	I/O	GPIO	MICLDO: MIC Power Supply; ADC0: ADC Input Channel 0;
38	ACM	P		Audio analog reference bias;
39	AVSS	G		Audio analog ground;
40	VCM	P		Audio ADC/DAC reference;
PAD	VSS	G		System Ground;

Pin Type	Description	Pin Type	Description
P	Power	I/O	Input or Output
PO	Power Output	I	Input
PI	Power Input	O	Output
G	Ground	RFI	Radio frequency interface
AO	Analog Output		

3 Electrical Characteristics

3.1 Absolute Maximum Ratings

Table 3-1

Symbol	Parameter	Min	Max	Unit
T _{opt}	Operating temperature	-40	+85	°C
T _{stg}	Storage temperature	-65	+150	°C
V _{BAT}	Supply Voltage	-0.3	4.5	V
V _{PWR}	Charger Voltage	-0.3	6	V
V _{IOVDD}	Voltage applied at IOVDD	-0.3	3.6	V
V _{GPIO}	Voltage applied to GPIO	-0.3	IOVDD+0.3	V
V _{HVIO}	Voltage applied to High Voltage Resistant IO	-0.3	+5.5	V
V _{HPVDD}	Voltage applied at HPVDD	-0.3	+3	V

Note : The chip can be damaged by any stress in excess of the absolute maximum ratings listed below

3.2 PMU Characteristics

Table 3-2

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
V _{BAT}	Voltage Input	2.2	3.7	4.4	V	
V _{PWR}	Charger supply Voltage	4.5	5.0	5.5	V	
Operating mode						
IOVDD	Voltage output	–	3.0	–	V	V _{BAT} = 4.2V, 10mA loading
	Loading current	–	–	200	mA	IOVDD=3.2V@V _{BAT} = 3.5V
DCVDD	Voltage output	–	1.25	–	V	IOVDD=3.0V, 10mA loading
	Loading current	–	–	100	mA	DCVDD=1.25V@IOVDD=3.0v on LDO mode
		–	–	180	mA	DCVDD=1.25V@V _{BAT} =3.0v on DCDC mode
EVDD	Voltage output	–	1.1	–	V	DCVDD=1.25V, 1mA loading
	Loading current	–	–	5	mA	EVDD=1.1V@DCVDD=1.25v
Low Power mode						
IOVDD	Loading current	–	–	10	mA	IOVDD=3V@V _{BAT} = 4.2V

3.3 Battery Charge

Table 3-3

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
VPWR	Charge Input Voltage	4.5	5	5.5	V	-
V _{bat float}	Charge Voltage	4.15	4.2	4.25	V	VPWR > 4.5V
		4.30	4.35	4.40	V	VPWR > 4.65V
I _{bat}	Charge Current	15	-	200	mA	Charge current at fast charge mode VBAT=4.0V@VPWR=5.0V
I _{end}	End Of Charge Current	2	-	30	mA	End of charge current
V _{Trickl}	Trickle Charge Voltage	-	3.0	-	V	VPWR > 4.5V
I _{Trickl}	Trickle Charge Current	1.5	-	30	mA	V _{BAT} < V _{Trickl}

3.4 IO Input/Output Electrical Logical Characteristics

Table 3-4

GPIO input characteristics						
Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
V _{IL}	Low-Level Input Voltage	-0.3	-	0.3* IOVDD	V	IOVDD = 3.0V
V _{IH}	High-Level Input Voltage	0.7* IOVDD	-	IOVDD+0.3	V	IOVDD = 3.0V
High Voltage Resistant IO input characteristics						
Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
V _{IL}	Low-Level Input Voltage	-0.3	-	0.3* IOVDD	V	IOVDD = 3.0V
V _{IH}	High-Level Input Voltage	0.7* IOVDD	-	+5V	V	IOVDD = 3.0V
GPIO & High Voltage Resistant IO output characteristics						
Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
V _{OL}	Low-Level Output Voltage	-	-	0.1* IOVDD	V	IOVDD = 3.0V
V _{OH}	High-Level Output Voltage	0.9* IOVDD	-	-	V	IOVDD = 3.0V

3.5 Internal Resistor Characteristics

Table 3-5

Port	Drive(mA)		Internal Pull-Up Resistor	Internal Pull-Down Resistor	Comment
PA0~PA6	HD,HD0==0,0	2.4	10K	10K	1、PB1 default pull up 2、USBDM & USBDP default pull Down 3、internal pull-up / pull-down resistance accuracy ±20%
PC1~PC5	HD,HD0==0,1	8			
PG5~PG8	HD,HD0==1,0	26			
PE5 , PE6	HD,HD0==1,1	46			
PP0	8		10K	10K	
PB1~PB8	8		10K	10K	
USBDP	4		1.5K	15K	
USBDM			180K	15K	

3.6 DAC Characteristics

Table 3-6

Parameter	Min	Typ	Max	Unit	Audio Format	Test Conditions
Frequency Response	20	—	20k	Hz	—	Differential Mode 1KHz/0dB 32 ohm loading With A-Weighted Filter
Output Swing	—	1	—	Vrms	—	
THD+N	—	-77	—	dB	PCM	
	—	-70	—	dB	SBC	
S/N	—	105	—	dB	PCM	
	—	105	—	dB	SBC	
Crosstalk	—	-110	—	dB	—	1KHZ/0dB 10k ohm loading
Dynamic Range	—	104	—	dB	PCM	Differential Mode 1KHz/-60dB 32 ohm loading With A-Weighted Filter
	—	104	—	dB	SBC	
Noise Floor	—	5.6	—	uVrms	—	A-Weighted Filter
DAC Output Power	—	32	50	mW	—	Differential Mode 32ohm loading

3.7 ADC Characteristics

Table 3-7

Parameter	Min	Typ	Max	Unit	Test Conditions
Dynamic Range		94		dB	Fsample=44.1kHz,Gain=0dB Fin=1KHz 590mVrms
SNR	-	95	-	dB	Fsample=44.1kHz,Gain=0dB Fin=1KHz 590mVrms
THD+N	-	-75	-	dB	
SNR	-	76	-	dB	Fsample=44.1kHz,Gain=18dB Fin=1KHz 75mVrms
THD+N	-	-73	-	dB	

3.8 BT Characteristics

3.8.1 Transmitter

Basic Rate

Table 3-8

Parameter	Min	Typ	Max	Unit	Test Conditions
RF Transmit Power		7	9	dBm	25°C, Power Supply VBAT=3.7V 2441MHz
RF Power Control Range		18		dB	
20dB Bandwidth		950		KHz	
In-band spurious Emissions (BQB Test Mode RF_Tx Power=5dBm)	F=F ₀ ±1MHz	-22		dBm	
	F=F ₀ ±2MHz	-51		dBm	
	F=F ₀ ±3MHz	-55		dBm	
	F=F ₀ +/->3MHz	-55		dBm	

Enhanced Data Rate

Table 3-9

Parameter	Min	Typ	Max	Unit	Test Conditions
Relative Power		-2		dB	25°C, Power Supply VBAT=3.7V 2441MHz
$\pi/4$ DQPSK Modulation Accuracy	DEVM RMS	7		%	
	DEVM 99%	17		%	
	DEVM Peak	14		%	
In-band spurious Emissions (BQB Test Mode RF_Tx Power=5dBm)	F=F ₀ ±1MHz	-4		dBm	
	F=F ₀ ±2MHz	-34		dBm	
	F=F ₀ ±3MHz	-43		dBm	
	F=F ₀ +/->3MHz	-48		dBm	

3.8.2 Receiver

Basic Rate

Table 3-10

Parameter		Min	Typ	Max	Unit	Test Conditions
Sensitivity			-92		dBm	25°C, Power Supply VBAT=3.7V 2441MHz DH5
Co-channel Interference Rejection			10		dB	
Adjacent channel selectivity C/I	+1MHz		-4		dB	
	-1MHz		-3		dB	
	+2MHz		-39		dB	
	-2MHz		-33		dB	
	+3MHz		-45		dB	
	-3MHz		-28		dB	

Enhanced Data Rate

Table 3-11

Parameter		Min	Typ	Max	Unit	Test Conditions
Sensitivity		-95	-94		dBm	25°C, Power Supply VBAT=3.7V 2441MHz 2DH5
Co-channel Interference Rejection			10		dB	
Adjacent channel selectivity C/I	+1MHz		-8		dB	
	-1MHz		-8		dB	
	+2MHz		-40		dB	
	-2MHz		-33		dB	
	+3MHz		-45		dB	
	-3MHz		-27		dB	

3.8.3 BLE

1M Data Rate

Table 3-12

Parameter		Min	Typ	Max	Unit	Test Conditions
Sensitivity			-96		dBm	25°C Power Supply VBAT=3.7V 2440MHz
RF Transmit Power			7		dBm	
In-band Spurious Emission	$ M-N =2\text{MHz}$		-39		dBm	
	$ M-N \geq 3\text{MHz}$			-41	dBm	
Modulation Characteristics	$\Delta f1$ avg		250		KHz	
	$\Delta f2$ 99%		209		KHz	
	$\Delta f1\text{avg}/\Delta f2\text{avg}$		0.9			
Carrier Frequency Offset		-10		+10	KHz	
Frequency Drift		-10		+10	KHz	
Frequency Drift Rate		-5		+5	KHz/50us	

2M Data Rate**Table 3-13**

Parameter		Min	Typ	Max	Unit	Test Conditions
Sensitivity			-94		dBm	25°C Power Supply VBAT=3.7V 2441MHz
RF Transmit Power			7		dBm	
In-band Spurious Emission	M-N =4MHz		-44		dBm	
	M-N =5MHz		-41		dBm	
	M-N ≥6MHz			-43	dBm	
Modulation Characteristics	Δf1 avg		500		KHz	
	Δf2 99%		422		KHz	
	Δf1avg/Δf2avg		0.9			
Carrier Frequency Offset		-10		+10	KHz	
Frequency Drift		-15		+15	KHz	
Frequency Drift Rate		-5		+5	KHz/50us	

Long Range**Table 3-14**

Parameter	Min	Typ	Max	Unit	Test Conditions
Sensitivity LE 125K(S8)		-104		dBm	VBAT=3.7V,25°C
Sensitivity LE 500K(S2)		-100		dBm	2441MHz

3.9 ESD Protection**Table 3-15**

Parameter	Typ.	Test pin	Reference standard
Human Body Mode	±4KV	All pins	JEDEC EIA/JESD22-A114
Machine Mode	±200V	All pins	JEDEC EIA/JESD22-A115
Charge Device Model	±1KV	All pins	JEDEC EIA/JESD22-C101F
Latch up	±200mA	All GPIO pins	JEDEC STANDARD NO.78E
	1.5xVopmax	All power pins	

Note : 1.5xVopmax = 1.5 times maximum operating voltage.

4 Package Information

4.1 QFN40_5.0x5.0

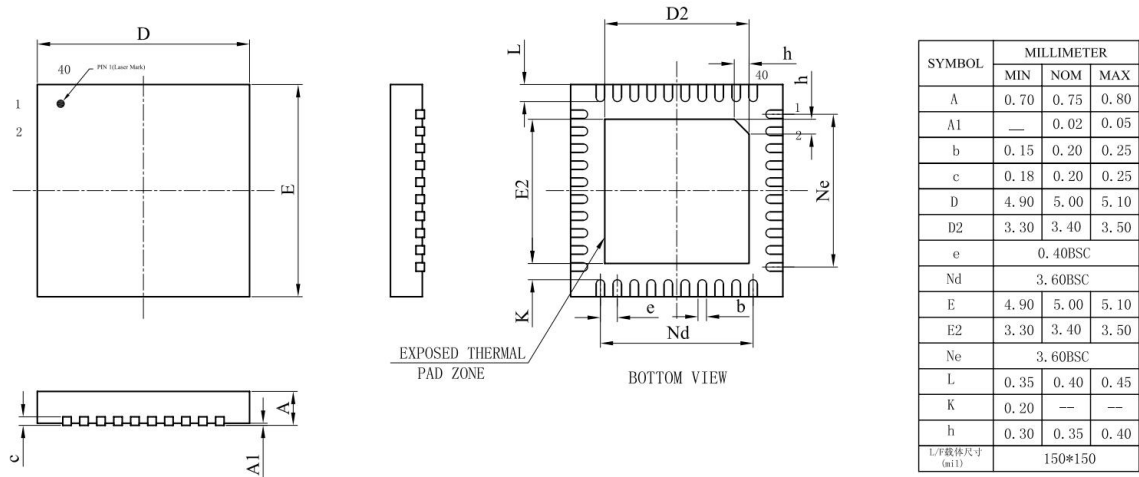
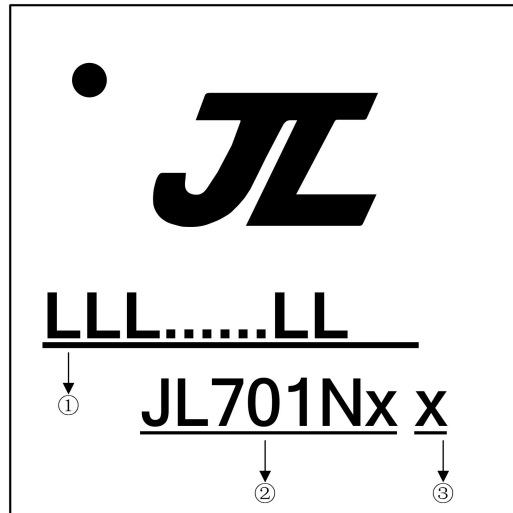


Figure 4-1 JL7018M Package

5 IC Marking Information



- ① LLL.....LL: LOT No. , It contains 7 to 18 alphanumerics
- ② JL701Nx: Chip Model
- ③ x: Built-in flash size
 - 0: No Flash Memory
 - 2: 2Mbit Flash
 - 4: 4Mbit Flash
 - 8: 8Mbit Flash
 - 6: 16Mbit Flash
 - 3: 32Mbit Flash

6 Solder-Reflow Condition

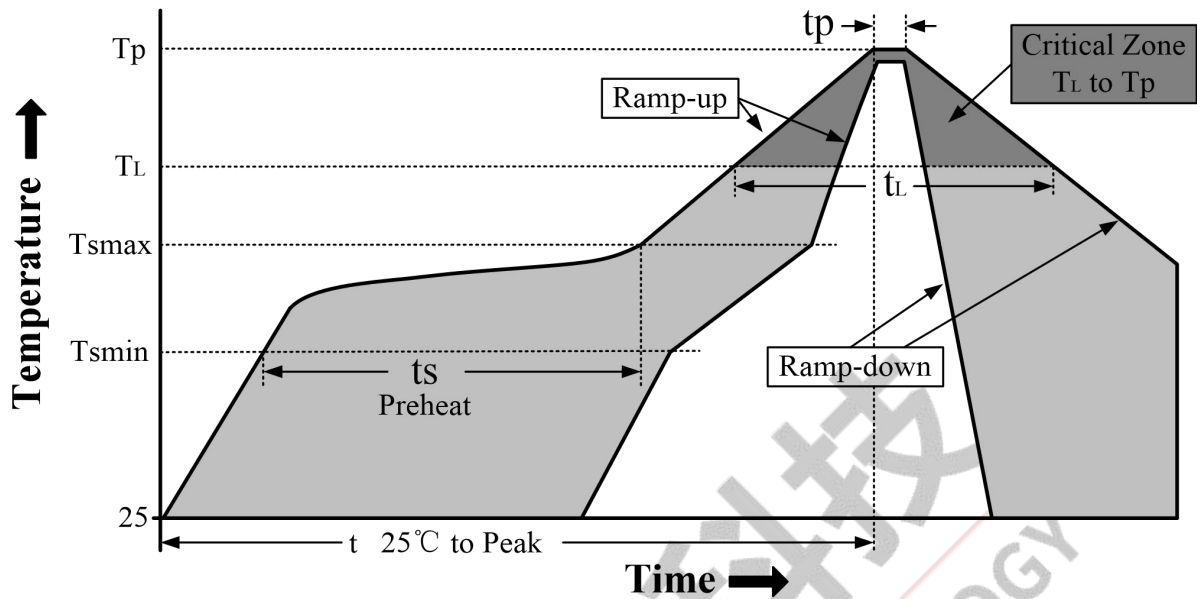


Figure 6-1 Classification Reflow Profile

Classification Profiles

Table 6-1

Profile Feature		Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat/ Soak	Temperature Min (T_{smin})	100°C	150°C
	Temperature Max (T_{smax})	150°C	200°C
	Time (t_s) from (T_{smin} to T_{smax})	60-120 seconds	60-180 seconds
Average ramp-up rate (T_{smax} to T_p)		3°C/second max	3°C/second max
Liquidous temperature (T_L)		183°C	217°C
Time (t_L) maintained above T_L		60-150 seconds	60-150 seconds
Peak package body temperature (T_p)		See Table 6-2	See Table 6-3
Time within 5°C of actual Peak Temperature (t_p) ²		10-30 seconds	20-40 seconds
Ramp-down rate (T_p to T_L)		6°C/second max	6°C/second max
Time 25°C to peak temperature		6 minutes max	8 minutes max

Note 1: All temperatures refer to topside of the package, measured on the package body surface.

Note 2: Time within 5°C of actual peak temperature (t_p) specified for the reflow profiles is a “supplier” minimum and “user” maximum.

SnPb - Classification Temperature

Table 6-2

Package Thickness	Volume mm ³ < 350	Volume mm ³ ≥ 350
<2.5 mm	240 +0/-5°C	225 +0/-5°C
≥2.5 mm	225 +0/-5°C	225 +0/-5°C

Pb-free - Classification Temperature **Table 6-3**

Package Thickness	Volume mm³ < 350	Volume mm³ 350 - 2000	Volume mm³ > 2000
< 1.6mm	260°C	260°C	260°C
1.6 mm - 2.5mm	260°C	250°C	245°C
> 2.5mm	250°C	245°C	245°C



7 Storage Condition

7.1 Moisture Sensitivity Level

JL7018M is qualified to moisture sensitivity level MSL3 in accordance with JEDEC J-STD-033.

7.2 Storage Alert

1. Calculated shelf life in sealed bag 12 months at $<40^{\circ}\text{C}$ and 90% relative humidity (RH).
2. Peak package body temperature $\leq 260^{\circ}\text{C}$.
3. After bag is opened, devices that will be subjected to reflow solder or other high temperature process must be mounted within 168 hours of factory conditions $\leq 30^{\circ}\text{C}/60\%\text{RH}$ or stored per J-STD-033.
4. Devices require bake before mounting if humidity indicator card reads $> 10\%$ for level 2a-5a devices or $> 60\%$ for level 2 devices when read at $23 \pm 5^{\circ}\text{C}$, or 3a or 3b are not met.
5. Please refer to IPC/JEDEC J-STD-033 for baking procedure if necessary.

8 Revision History

Date	Revision	Description
2022.07.20	V1.0	Initial Release
2022.09.20	V1.1	Add Storage Condition and ESD Protection; Update IC Marking Information and BT characteristics
2023.02.22	V1.2	Update Features and Pin Description
2023.03.01	V1.3	Update Features
2023.10.17	V1.4	Update JL7018M BT_Features
2023.12.29	V1.5	Update JL7018M BT_Features (Meet class1 transmitting power requirement)
2024.08.09	V1.6	Update Audio & PMU_Features Update IC Marking Information